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A DEVELOPING METHOD AND APPARATUS FOR PERFORMING
DEVELOPMENT PROCESSING PROPERLY AND A SOLUTION PROCESSING
METHOD ENABLING ENHANCED UNIFORMITY IN THE PROCESSING

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Background of the Invention

1. Field of the Invention

The present invention relates to a developing method
and apparatus that supply a developing solution to a
surface of a substrate, for example, on which a resist
10 is coated and subjected to exposure, to perform
development processing and a solution processing method
enabling enhanced uniformity in the processing.

2. Description of the Related Art

It is generally known to use techniques of
15 photolithography using photoresist in forming electronic
materials such as substrates, for example, semiconductor
wafers. An example of the techniques is disclosed in
Japanese Laid-Open Patent Publication No. H02-296316.

The technique discloses a paddle development scheme
20 as development processing, where during the progress of
development on a substrate, instead of holding the
substrate on a rotating stage movable upwardly and
downwardly, the substrate is supported by a ring
supporting frame which is configured to enable the
25 substrate to be provided and received to/from the rotating
stage and is provided with a rubber ring coming into contact
with a back of the substrate, and development is performed

in a cover.

Further, another example of the techniques is disclosed in Japanese Patent No.3257038.

In this technique, during the progress of development on a substrate, instead of holding the substrate on a rotating stage, the substrate is supported by an isolating member which is configured to enable the substrate to be provided and received to/from the rotating stage and to move upwardly and downwardly and is provided with a pin coming into point-contact with a back of the substrate, and development is performed in a cup under downflow with controlled temperature and moisture.

Summary of the Invention

However, since the substrate is placed nearby an inject opening of the downflow with controlled temperature and moisture after supplying a developing solution to the substrate, there is a fear that the developing solution on the substrate spills by increased effect of the downflow, resulting in a factor for decreasing the yield in the development processing. Further, since the developing solution is supplied to a substrate in a cup to proceed the development while exhausting the downflow with controlled temperature and moisture from the cup, the downflow has a significant effect on the developing solution on the substrate, and there is a fear that the developing solution on the

substrate spills by increased effect of the downflow, resulting in a factor for decreasing the yield in the development processing.

Furthermore, after separating the substrate from the rotating stage by the isolating member or ring supporting frame with the rubber ring, or in mounting the substrate on the rotating stage, mists of the developing solution and/or rinsing solution reach the back of the substrate, and adhere to the isolation member, ring supporting frame with the rubber ring and/or the rotating stage. Then, the mists are generated in the processing chamber when the solution(s) dries, or the solutions adhered to the back of the substrate become mists in a subsequent processing chamber or during carriage of the substrate, and thus the whole processing apparatus is polluted, resulting in factors for decreasing not only the field in the development processing but also the yield in the entire substrate processing.

20 An object of the present invention is to provide a developing method and apparatus for performing development processing properly and a solution processing method enabling enhanced uniformity in the processing

In order to achieve the object, a first aspect of the present invention is a method of developing an exposed resist on a processing surface of a substrate in a cup, where the method has the steps of supporting or holding

a side opposed to the processing substrate of the substrate and supplying a developing solution to the processing surface of the substrate and the cup, or to the processing surface of the substrate, exhausting air from a first
5 peripheral region outside the cup during the progress of substantial development processing with the side opposed to the processing surface of the substrate held, and exhausting air from a second peripheral region inside the cup or from the second peripheral region and the first
10 peripheral region in a rinsing process with the substrate held in vacuum adsorption.

A second aspect of the present invention is an apparatus that develops an exposed resist on a processing surface of a substrate, where the apparatus has a first
15 enclosing member disposed around the substrate, a second enclosing member disposed around the first enclosing member, a supporting mechanism that is disposed inside the first enclosing member and supports the substrate, a holding mechanism that is disposed inside the first
20 enclosing member and holds the substrate in vacuum adsorption, and an exhausting mechanism that exhausts air from a region between the first enclosing member and the second enclosing member when the substrate is supported by the supporting mechanism.

25 A third aspect of the present invention is a method of supplying a processing solution to a substrate to process, where the method has the steps of exhausting

air from a first peripheral region around the substrate,
and exhausting air from a second peripheral region between
the first peripheral region and the substrate and from
the first peripheral region, or from the second peripheral
5 region.

The present invention allows exhaust primarily from
the first peripheral region around the substrate
undergoing processing, and further from the second
peripheral region between the first peripheral region
10 and the substrate. Therefore, the present invention
enables reduced effects of currents of air on a processing
solution, for example, developing solution on a
processing surface of the substrate, further enables the
developing solution used in development to properly act
15 on the exposed resist on the substrate, and thus enhances
the uniformity in the processing on the substrate and
improves the yield in the processing on the substrate.

The above and further objects and features of the
present invention will more fully be apparent from the
20 following detailed description with the accompanying
drawings.

Brief Description of the Drawings

FIG.1 is a plan view showing an entire structure
25 of a coating/developing apparatus according to one
embodiment of the present invention;

FIG.2 is a schematic sectional view showing one

embodiment of a development processing section (DEV) shown in FIG.1;

FIG.3A is a schematic perspective view to explain a supporting mechanism of a primary portion of the development processing section (DEV) in FIG.2;

FIG.3B is a schematic sectional view to explain the supporting mechanism of the primary portion of the development processing section (DEV) in FIG.2;

FIG.4A is a schematic plan view to explain a development processing section (DEV) in FIG.2;

FIG.4B is a schematic sectional view to explain the primary portion of the development processing section (DEV) in FIG.2;

FIG.4C is another schematic sectional view to explain the primary portion of the development processing section (DEV) in FIG.2;

FIG.4D is another schematic sectional view to explain the primary portion of the development processing section (DEV) in FIG.2;

FIG.5 is a schematic sectional view showing one embodiment of a coating processing section (COT);

FIG.6 is a schematic plan view to explain the coating processing section (COT) in FIG.5;

FIG.7A is a schematic perspective view to explain a supporting mechanism in another embodiment of the development processing section (DEV);

FIG.7B is a schematic sectional view to explain the

supporting mechanism in another embodiment of the development processing section (DEV);

FIG.8A is a schematic sectional view showing a primary portion in another embodiment of the development
5 processing section (DEV);

FIG.8B is another schematic sectional view showing the primary portion in another embodiment of the development processing section (DEV);

FIG.9 is a schematic perspective view showing an
10 embodiment of another cup in the development processing section (DEV);

FIG.10 is a schematic sectional view showing another embodiment of the development processing section (DEV);

FIG.11 is a schematic plan view to explain the
15 development processing section (DEV) in FIG.10;

FIG.12A is a schematic perspective view to explain a supporting mechanism in another embodiment of the development processing section (DEV);

FIG.12B is a schematic sectional view to explain
20 the supporting mechanism in another embodiment of the development processing section (DEV);

FIG.13 is a schematic sectional view to explain a holding mechanism in still another embodiment of the development processing section (DEV);

25 FIG.14 is a schematic sectional view to explain a supporting mechanism in still another embodiment of the development processing section (DEV); and

FIG.15 is a perspective view to explain a location where a storage container that stores a processing solution is placed in a solution processing apparatus.

5 Detailed Description of the Preferred Embodiments

Embodiments of the present invention will be described below specifically with reference to the accompanying drawings.

FIG.1 is a schematic plan view showing an entire
10 structure of a coating/developing apparatus as a solution processing apparatus, for example, resist processing apparatus according to one embodiment.

A resist processing apparatus 1 has in its primary portion a cassette unit section CU having a cassette mount
15 section U1 enabling itself to mount a plurality of cassettes C thereon where each cassette enables itself to store a plurality of substrates, for example, semiconductor wafers W, and a substrate carrying in/out mechanism section U2 having a substrate carrying in/out
20 mechanism 2 enabling each semiconductor wafer W to be carried in or out of a cassette C in the cassette mount section U1 on a sheet basis, an interface unit IFU section having a providing section 4 that provides each semiconductor wafer W on a sheet basis to another apparatus,
25 for example, an exposure apparatus 3 that performs exposure processing on the semiconductor wafer W, a receiving section 5 that receives each semiconductor

wafer W on a sheet basis from the exposure apparatus 3 and a substrate carrying in/out mechanism 6 enabling each semiconductor wafer W to be carried in or out on a sheet basis, and a process unit section PU having processing sections that perform predetermined processing on the semiconductor wafer W, for example, as solution processing section, a coating processing section COT that coats a resist solution, a development processing section DEV that develops the exposed resist on the semiconductor wafer W, a check processing section 7 that checks a state of the resist film on the semiconductor wafer W at predetermined timing for the semiconductor wafer W, substrate providing/receiving sections 8 and 9 enabling each semiconductor wafer W to be carried in or out of the substrate carrying in/out mechanisms 2 and 6 on a sheet basis, respectively, and a substrate carrying mechanism 10 enabling each semiconductor wafer W to be provided on a sheet basis to the substrate providing/receiving sections 8 and 9, coating processing section COT, development processing section DEV and check processing section 7.

In addition, arms 11 and 12 in the substrate carrying in/out mechanisms 2 and 6 which hold the semiconductor wafers W in vacuum adsorption or support periphery portions of semiconductor wafers W in point-contact or in line-contact are movable in vertical directions Z1 and Z2, in the forward/backward directions Y1 and Y2 and

in rotation directions $\theta 1$ and $\theta 2$, as viewed in the figure, and bases 13 and 14 of the arms 11 and 12 are movable in the horizontal directions X1 and X2 as viewed in the figure together with the arms 11 and 12, respectively.

5 An arm 17 of the substrate carrying mechanism 10 in the process unit section PU holds the periphery portion of a semiconductor wafer W in point-contact or in line-contact, and is movable in the vertical direction Z0, in the forward/backward direction Y0 and in the
10 rotation direction $\theta 0$ as viewed in the figure. In addition, for convenience, the substrate carrying in/out mechanisms 2 and 6 and substrate carrying mechanism 10 are configured as described above. However, an articulated robot can be used, and it is only required
15 to provide the substrate carrying in/out mechanism section U2 and interface unit section IFU with carrying mechanisms capable of implementing the above-mentioned functions.

At a position below each of the substrate
20 providing/receiving sections 8 and 9 is provided a plurality of temperature adjusting sections (not shown) that is laminated and adjusts the temperature of the semiconductor wafer W to approximately the same temperature as that inside the processing chamber.
25 Further, at a position below the plurality of temperature adjusting sections is provided a plurality of gas processing sections (not shown) that is laminated and

executes processing on the semiconductor wafer W using processing gas such as, for example, HMD gas. At a position above each of the substrate providing/receiving sections 8 and 9 is provided a plurality of heating processing sections (not shown) that is laminated and heats the semiconductor wafer W to the predetermined temperature more than room temperature to execute processing.

Each of the substrate carrying mechanism 10 in the process unit section PU and the substrate carrying in/out mechanism 2 in the cassette unit section CU is capable of carrying the semiconductor wafer W in and out of the check processing section 7 in the process unit section PU, and therefore, it is possible to perform a check such as, for example, a thickness of the resist film on the semiconductor wafer W prior to the processing and the semiconductor wafer W subjected to the processing in each of the above-mentioned processing sections and/or exposure apparatus.

At a position above each of the substrate carrying in/out mechanism section U2 in the cassette unit section CU, the process unit section PU and the interface unit section IFU is provided a filter section (not shown), and the filter section supplies air with temperature and moisture respectively set at a predetermined value to a respective unit. Further, an exhaust opening provided under each of the unit sections recovers the air with

temperature and moisture set at a predetermined amount by a respective exhaust setting mechanism so as to enable downflow of the air with temperature and moisture to be formed in each unit section.

5 Respective exhaust setting mechanisms of the substrate carrying in/out mechanism section U2 in the cassette unit section CU, the process unit section PU and the interface unit section IFU set pressures such that the pressure inside the process unit section PU is
10 higher than that inside the substrate carrying in/out mechanism section U2 in the cassette unit section CU, that the pressure inside the process unit section PU is higher than that inside the interface unit section IFU, and that the pressure inside the exposure apparatus 3
15 is higher than that inside the interface unit section IFU, and thus prevent unnecessary mists from entering the process unit section PU and/or exposure apparatus 3 to be factors of having adverse effects on the processing on the semiconductor wafer W. As compared to oxygen
20 and/or acidic gases (such as NOX, SOX H₂S and CO₂) and/or basic gases (such as ammonia and amine) and/or moisture contained in the atmosphere inside cassette unit section CU, their amounts contained in the atmosphere inside the process unit section PU and/or interface unit section
25 IFU are set to be substantially smaller. It is because of reducing effects thereof on the processing particularly prior to or subsequent to exposure and thus

improving the yield of the processing on the semiconductor wafer W.

In addition, as described above, walls 20 are provided between the substrate carrying in/out mechanism section U2 in the cassette unit section CU and the process unit section PU and between the process unit section PU and the interface unit section IFU to interrupt atmospheres of the sections. Substrate in/out opening 19 of each of the substrate providing/receiving sections 8 and 9 and check processing section 7 is capable of being opened and closed by an opening/closing mechanism (not shown) for example, cover, except processes for carrying in and out the semiconductor wafer W, and thus is configured to interrupt each of the atmospheres of the substrate carrying in/out mechanism section U2 in the cassette unit section CU, the process unit section PU and the interface unit section IFU.

Coating processing sections COT in the process unit section PU are arranged as a plurality of laminates. Further, development-processing sections DEV are arranged as a plurality of laminates. With respect to these processing sections, the semiconductor wafer W can be carried in and out by the substrate carrying mechanism 10. In addition, temperatures and moistures inside the coating processing sections COT and/or development processing sections DEV are set predetermined values, and set to be higher than those in the process unit section

PU even when the exhaust states inside the processing sections change. It is because of preventing mists from entering the coating processing sections COT and/or development processing sections CEV and that are
5 solution-processing sections to be factors of having adverse effects on the processing on the semiconductor wafer W. Further, the atmosphere inside the processing sections COT and/or development processing sections DEV is set to be smaller than the atmosphere inside the process
10 unit section PU in amounts of oxygen and/or acidic gases (such as NOX, SOX H₂S and CO₂) and/or basic gases (such as ammonia and amine) and/or moisture contained in the atmosphere. It is because of reducing effects of such gases to improve the yield of the processing on the
15 semiconductor wafer W.

A structure of the development processing section DEV will be described below with respect to FIGs.2, 3A, 3B, 4A, 4B, 4C and 4D.

The development processing section DEV is provided
20 with at its upper portion an air supplying mechanism 30 that supplies the air with the temperature and moisture controlled to predetermined values to the processing chamber, and is configured to be maintained at
predetermined temperature and moisture based on detection
25 data in a sensor 30a provided in the processing chamber by a control mechanism 31.

At a lower position of the processing chamber is

provided a chuck 32 as a holding mechanism that holds the back of the semiconductor wafer W in vacuum adsorption. The chuck 32 is configured to be rotatable by a rotation driving mechanism, for example, a motor 33. In addition, 5 the chuck 32 is configured not to move upwardly and downwardly in this embodiment. Since the motor 33 needs to move upwardly and downwardly to cause the chuck 32 to move upwardly and downwardly, a range of thermal effects of the motor 33 on the apparatus becomes wider, and thus 10 a risk arises that the semiconductor wafer W undergoes the thermal effects and the yield decreases. Further, to suppress the thermal effects, a thermal suppressing mechanism under the processing chamber becomes large in system. For example, the vertical size of the processing 15 chamber needs to be thin as possible to arrange a plurality of such processing chambers to be laminated. However, in a system that does not require such a consideration, the chuck can be configured to move with the motor 33.

At a position below the chuck 32 is provided a 20 supporting mechanism 35 that supports the back of the semiconductor wafer W. As shown in FIGs. 3A and 3B, the supporting mechanism 35 is provided with a plurality of supporting pins 36 that supports the back of the semiconductor wafer W in point-contact, a ring member 25 37 as a solution penetration preventing mechanism that is provided outside the supporting pins 36 and prevents the processing solution such as the developing solution

and rinsing solution from entering a center portion of the back of the semiconductor wafer W, and a plurality of supporting poles 38 that supports in one piece the ring member 37 and supporting pins 36.

5 Further, as shown in FIG.3B, heights and positions of supporting pins 36 and ring member 37 are set so that supporting pins 36 are higher by a predetermined length, for example, a length to hold the processing solution between the back of the semiconductor wafer W and the
10 ring member 37 by surface tension of the processing solution such as the developing solution and/or rinsing solution, e.g. length more than 0.5 mm to prevent the contact with the semiconductor wafer W, e.g. length (L in the figure) ranging from 1.5 mm to 5 mm. It is because
15 of preventing the ring member 37 from coming into direct contact with the back of the semiconductor. A contact portion 38a of the supporting pin 36 to be in contact with the back of the semiconductor W is formed of, for example, an elastic member, as a member having a higher
20 coefficient of friction and lower thermal conductivity than those of a member 39 forming the supporting pin 36 and also as a displacement preventing member that prevents occurrences of horizontal displacements including horizontal displacements in supporting the back of the
25 semiconductor W and further in supplying the processing solution to the semiconductor wafer after supporting the back of the semiconductor W. The low thermal conductivity

prevents occurrences of a risk that the uniformity in the surface is inhibited due to effects such as the heat escaping from the semiconductor wafer W through the contact portion with the supporting pin 36 during the processing of the semiconductor wafer W. As materials for the contact portion 38a, examples include engineering plastics such as PEEK, PBI, ceramics such as alumina, zirconium and rubbers such as perfluoro-compounds.

Further, the ring member 37 is provided with at its head portion an asperity portion 40 (solution penetration preventing portion) as a solution holding portion that holds the developing solution and/or rinsing solution supplied to the semiconductor wafer W between the member 37 and the back of the semiconductor wafer W by surface tension. On an inner wall of the asperity portion 40 is provided a tilting portion 41 to cause the solution to escape smoothly. In addition, for conveniences, this embodiment describes the asperity portion 40 as a solution holding portion that holds the solution by surface tension. However, the solution-holding portion is not limited to the portion 40 as long as the portion has a mechanism that holds by surface tension.

As shown in FIG.2, the supporting mechanism 35 is configured to be movable upwardly and downwardly by a moving mechanism, for example, an air cylinder 50 for the supporting mechanism.

Further as shown in FIG.2, on an inner side of the

supporting mechanism 35 is provided a plurality of back
nozzles 51 as a rinsing solution back supply mechanism
that supplies the rinsing solution, for example, pure
water to the periphery portion of the semiconductor wafer
5 W on the back of the semiconductor wafer W or to the asperity
portion 40 of the ring member 37.

Around the chuck 32 is provided a cup 60 as a first
enclosing member configured to enclose the semiconductor
wafer W held by the chuck 32. At a position below the
10 cup 60 is provided a gas/liquid recovery opening 70 that
recovers at least part of the air from the air supplying
mechanism 30 and the developing solution and/or rinsing
solution, and a gas/liquid recovering mechanism 71 as
an exhaust mechanism recovers such air and liquid. The
15 gas/liquid recovery mechanism 71 is configured to be able
to set a recover amount of the air at an arbitrary
predetermined amount. In other words, a region (second
peripheral region β) to exhaust from inside the cup 60
is configured to enable an arbitrary predetermined amount
20 to be set. In addition, the cup 60 is configured to be
movable upwardly and downwardly by a cup moving mechanism
(not shown).

Around the cup 60 is disposed a wall portion 75 that
forms a wall of the processing chamber as a second enclosing
25 member provided to enclose the cup 60. At a position below
a region between the cup 60 and wall portion 75 is provided
a gas/liquid recovery opening 76 that recovers at least

part of the air from the air supplying mechanism 30 and the developing solution and/or rinsing solution through a rectifying mechanism 74 provided with a plurality of recovery openings 73 that rectifies the current of air, and a gas/liquid recovery mechanism 77 as an exhaust mechanism recovers such air and solution. The gas/liquid recovery mechanism 77 is configured to be able to set a recover amount of the air at an arbitrary predetermined amount. In other words, a region (first peripheral region α) to exhaust from the region between the cup 60 and wall portion 70 is configured to enable an arbitrary predetermined amount to be set.

Moreover, as shown in FIG.2, the wall portion 75 is provided with a carry-in/out opening 80 through which the arm 17 of the substrate carrying mechanism 10 that carries the semiconductor wafer W enters and escapes the processing chamber, and is further provided with a cover 81 as an opening and closing mechanism that opens and closes the carry-in/out opening 80 to interrupt the atmosphere between the processing chamber and an arrangement space of the substrate carrying mechanism 10 where the downflow DF is formed. In, addition, with respect to the relationship between the pressure inside the processing chamber and the arrangement space of the substrate carrying mechanism 10, the pressure inside the processing chamber is set higher. It is because of preventing, for example, particles from entering the

processing chamber from the arrangement space of the substrate carrying mechanism 10. Accordingly, based on detected data of a sensor 82 provided inside the arrangement space of the substrate carrying mechanism 10, the control mechanism 31 controls an air supply amount from the air supplying mechanism 30 and/or an air recovery amount from the gas/liquid recovery mechanism 77 and/or an air recovery amount from the gas/liquid recovery mechanism 71. When the arm 17 of the substrate carrying mechanism 10 enters the processing chamber, the cover 81 is opened and the pressure inside the processing chamber decreases. The change in pressure is detected by the sensor 82, and when the decreased pressure inside the processing chamber is higher than that inside the process unit section PU even the pressure inside the processing chamber decreases temporarily, it is not required to substantially vary, as compared to a set value during the processing of the semiconductor wafer W, a factor of varying the pressure inside the processing chamber, e.g. at least one factor among factors of air supply amount from the air supplying mechanism 30, air recovery amount from the gas/liquid recovery mechanism 77 and air recovery amount from the gas/liquid recovery mechanism 71. Further, when the cover 81 is opened and the pressure inside the processing chamber is approximately the same as the pressure inside the process unit section PU or is to be maintained in a predetermined pressure difference,

it is preferable to, before opening the cover 81, instead of varying the air supply amount from the air supply mechanism 30, vary at least one factor among the factors of the air recovery amount from the gas/liquid recovery mechanism 77 and air recovery amount from the gas/liquid recovery mechanism 71, in other words, it is preferable to decrease the recovery amount or halt to respond. The reason is that when the factor of varying the pressure is varied, a time is required to reach the value set during the processing of the semiconductor wafer W, and the throughput of the processing is reduced.

As shown in FIGs. 2, 4A and 4B, inside the processing chamber are provided a development nozzle 90 as a developing solution supplying mechanism that supplies the developing solution as a processing solution to the semiconductor wafer W and a rinse nozzle 91 as a rinsing solution supplying mechanism that supplies a rinsing solution as a processing solution such as, for example, pure water and/or an aqueous solution obtained by adding a surfactant to pure water to the semiconductor wafer W.

The development nozzle 90 is provided with, at a region larger by a predetermined length 93 than an inner diameter 92 of the cup 60, a discharging opening 94 that discharges the developing solution to discharge the developing solution to the cup 60 and the semiconductor wafer W at the same time. Further, the development nozzle

90 is configured to be movable in the direction X5 in the figure by a moving mechanism (not shown), starts discharging at least X51 above the cup 60, while moving to a discharge end position that is at least an end side X53 of the semiconductor wafer W (preferably X54 on above the cup 60), and is configured to enable the developing solution to be filled on the semiconductor wafer W.

With respect to the positional relationship in filled solution between the cup 60 and chuck 32, as shown in FIGs. 4B and 4C, the developing solution 95 discharged by the development nozzle 90 from above the cup 60 moves horizontally in the direction A 5 to proceed. With respect to the relationship in height between the cup 60 and the processing surface of the semiconductor wafer W held by chuck 32 or supported by the supporting mechanism 35, the processing surface of the semiconductor wafer W is set to be positioned at a position with the same height as that of cup 60 or at a position of height V10 higher than the cup 60, and is capable of being set in distance X10 between the cup 60 and the semiconductor wafer W held by the chuck 32 or supported by the supporting mechanism 35 due to relative movement between the cup 60 and/or the chuck 32 or supporting mechanism 35. It is preferable to set such distances i.e. distances V10 and X10 between the semiconductor wafer W and cup 60 so that the developing solution is held but does not remain between the semiconductor wafer W and the cup 60 by surface

tension of the developing solution discharged from the development nozzle 90. Excessively larger distances V10 and X10 between the semiconductor wafer W and cup 60 cause the developing solution to be supplied only to the semiconductor wafer W and are not preferable. In other words, it is preferable to set V10 and X10 at distances such that during the time the development nozzle 90 is moving in the direction X5, the developing solution discharged from the development nozzle 90 is temporarily held between the semiconductor wafer W and cup 60 by surface tension, but is not held anymore between the semiconductor wafer W and cup 60 by surface tension as the development nozzle 90 moves (in other words, distances such that the developing solution is temporarily held between the semiconductor wafer W and cup 60 by surface tension when the developing solution is supplied from the development nozzle 90, and that at a portion where the developing solution is not supplied as the development nozzle 90 moves, the developing solution is pulled between the semiconductor wafer W and cup 60 by surface tension and cannot be held anymore between the semiconductor wafer W and cup 60 (these distances are set as appropriate with type of developing solution). In this way, the developing solution of unnecessary amount in development slides down a tilting portion 60a or falls into the cup 60 to be recovered, and an appropriate amount of developing solution is filled on the semiconductor wafer W. As

another embodiment, as shown in FIG.4D, the height of the cup 60 is set at distance V100 that is higher than approximately the same height as that of the semiconductor wafer W, for example, higher than height of the developing solution 600 filled on the semiconductor wafer W. It is also possible to set in this way to generate the above-mentioned effects. In addition, the same setting can be used in chuck 32. Further, since the height of the cup 60 is set at distance V100 that is higher than approximately the same height as that of the semiconductor wafer W, it is possible to prevent effects of currents of air due to exhaust from outside the cup 60 from acting on the developing solution filled on the processing surface of semiconductor wafer W and to improve the yield in the processing.

Moreover, as shown in FIGs.2 and 4A, in the processing chamber is provided an arm 98 as an arm moving mechanism movable in the rotation direction θ 5 on an axis portion 97 as a supporting point. On a front portion of the arm 98 is provided the rinse nozzle 91 that supplies to the semiconductor wafer W a rinsing solution as a processing solution, for example, pure water or pure water containing a predetermined amount of surfactant. Movement of the arm 98 enables the rinse nozzle 91 to supply the rinsing solution to the center portion and its vicinity of the processing surface of the semiconductor wafer W.

A structure of the coating processing section COT

will be described with reference to FIG.5.

The coating processing section COT is provided with at its upper portion an air supplying mechanism 100 that supplies the air with the temperature and moisture controlled to predetermined values to the processing chamber, and is configured to be maintained at predetermined temperature and moisture based on detection data in a sensor 101 provided in the processing chamber by the control mechanism 31.

At a lower position of the processing chamber is provided a chuck 102 as a holding mechanism that holds the back of the semiconductor wafer W in vacuum adsorption. The chuck 102 is configured to be rotatable by a rotation driving mechanism, for example, a motor 103. In addition, the chuck 102 is configured not to move upwardly and downwardly in this embodiment. Since the motor 103 needs to move upwardly and downwardly to cause the chuck 102 to move upwardly and downwardly, a range of thermal effects of the motor 103 on the apparatus becomes wider, and thus a risk arises that the semiconductor wafer W undergoes the thermal effects and the yield decreases. Further, to suppress the thermal effects, a thermal suppressing mechanism under the processing chamber becomes large in system. For example, the vertical size of the processing chamber needs to be thin as possible to arrange a plurality of such processing chambers to be laminated. However, in a system that does not require such a consideration,

the chuck can be configured to move with the motor 103.

At a position below the chuck 102 is provided a supporting mechanism 104 that supports holds the back of the semiconductor wafer W. The supporting mechanism 104 has a plurality of supporting pins 105 that supports the back of the semiconductor wafer W in point-contact, and is configured to be movable by a moving mechanism, for example, an air cylinder 106 that integrally moves the chuck and pins.

Further, on an inner side of the supporting mechanism 104 is provided a plurality of back nozzles 107 as a solvent liquid back supply mechanism that supplies a solvent liquid, for example, thinner liquid to the periphery portion of the processing surface of the semiconductor wafer W on the back of the semiconductor wafer W.

Around the chuck 102 is provided a cup 110 as a first enclosing member configured to enclose the semiconductor wafer W held by the chuck 102. At a position below the cup is provided a gas/liquid recovery opening 111 that recovers at least part of the air from the air supplying mechanism 100 and the coating solution and/or rinsing solution, and a gas/liquid recovery mechanism 112 as an exhaust mechanism recovers such air and liquid. The gas/liquid recovery mechanism 112 is configured to be able to set a recover amount of the air at an arbitrary predetermined amount. In other words, a region (second peripheral region β) to exhaust from inside the cup 110

is configured to enable an arbitrary predetermined amount to be set. In addition, the cup 110 is configured to be movable upwardly and downwardly by a cup moving mechanism (not shown).

5 Around the cup 110 is disposed a wall portion 113 that forms a wall of the processing chamber as a second enclosing member provided to enclose the cup 110. At a position below a region between the cup 110 and wall portion 113 is provided a gas recovery opening 116 that recovers
10 at least part of the air from the air supplying mechanism 100 through a rectifying mechanism 115 provided with a plurality of recovery openings 114 that rectifies the current of air, and a gas recovery mechanism 117 as an exhaust mechanism recovers such air. The gas recovery
15 mechanism 117 is configured to be able to set a recover amount of the air at an arbitrary predetermined amount. In other words, a region (first peripheral region α) to exhaust from the region between the cup 100 and wall portion 113 is configured to enable an arbitrary predetermined
20 amount to be set.

 Moreover, the wall portion 113 is provided with a carry-in/out opening 120 through which the arm 17 of the substrate carrying mechanism 10 that carries the semiconductor wafer W enters and escapes the processing
25 chamber, and is further provided with a cover 121 as an opening and closing mechanism that opens and closes the carry-in/out opening 120 to interrupt the atmosphere

between the processing chamber and an arrangement space of the substrate carrying mechanism 10 where the downflow DF is formed. In, addition, with respect to the relationship between the pressure inside the processing chamber and the arrangement space of the substrate carrying mechanism 10, the pressure inside the processing chamber is set higher. It is because of preventing, for example, particles from entering the processing chamber from the arrangement space of the substrate carrying mechanism 10. Accordingly, based on detected data of the sensor 82 provided inside the arrangement space of the substrate carrying mechanism 10, the control mechanism 31 controls an air supply amount from the air supplying mechanism 100 and/or an air recovery amount from the gas recovery mechanism 117 and/or an air recovery amount from the gas/liquid recovery mechanism 112. When the arm 17 of the substrate carrying mechanism 10 enters the processing chamber, the cover 121 is opened and the pressure inside the processing chamber decreases. The change in pressure is detected by the sensor 101, and when the decreased pressure inside the processing chamber is higher than that inside the process unit section PU even the pressure inside the processing chamber decreases temporarily, it is not required to substantially vary, as compared to a set value during the processing of the semiconductor wafer W, a factor of varying the pressure inside the processing chamber, e.g. at least one factor

among factors of air supply amount from the air supplying mechanism 100, air recovery amount from the gas recovery mechanism 117 and air recovery amount from the gas/liquid recovery mechanism 112. Further, when the cover 121 is
5 opened and the pressure inside the processing chamber is approximately the same as the pressure inside the process unit section PU or is to be maintained in a predetermined pressure difference, it is preferable to, before opening the cover 121, instead of varying the air
10 supply amount from the air supply mechanism 100, vary at least one factor among the factors of the air recovery amount from the gas recovery mechanism 117 and air recovery amount from the gas/liquid recovery mechanism 112, in other words, it is preferable to decrease the recovery
15 amount or halt to respond. The reason is that when the factor of varying the pressure is varied, a time is required to reach the value set during the processing of the semiconductor wafer W, and the throughput of the processing is reduced.

20 Moreover, as shown in FIGs. 5 and 6, in the processing chamber is provided an arm 130 as an arm moving mechanism movable in the rotation direction θ 10 on an axis portion 131 as a supporting point. On a front portion of the arm 130 is provided a resist nozzle group 132 that supplies
25 to the semiconductor wafer W a plurality of kinds of coating solutions as a processing solution, for example, a resist solution. Movement of the arm 130 enables a specific

resist nozzle 134 selected from the resist nozzle group 132 to supply the resist solution to the center and its vicinity of the processing surface of the semiconductor wafer W. The arm 130 is configured to enable itself to
5 extend and shrink (in the direction 133 in the figure) to maintain the supply by the specific resist nozzle 134 selected from among the resist nozzle group 132 to the center and its vicinity of the processing surface of the semiconductor W at a constant position.

10 Further, as shown in FIGs. 5 and 6, in the processing chamber is provided an arm 140 as an arm moving mechanism movable in the rotation direction θ 11 on an axis portion 141 as a supporting point. On a front portion of the arm 140 is provided a solvent nozzle 142 that supplies to
15 the semiconductor wafer W a solvent liquid, for example, thinner liquid. Movement of the arm 140 enables the solvent nozzle 142 to supply the solvent liquid to the periphery portion of the processing surface of the semiconductor wafer W. It is configured to remove the
20 resist film on the periphery of the semiconductor wafer W among resist films coated on the processing surface of the semiconductor wafer W using the solvent liquid.

The operation of the resist processing apparatus 1 configured as described above will be described. First,
25 the cassette C storing a plurality of unprocessed semiconductor wafers W is placed in the cassette mount section U1 in the cassette unit section CU by an operator

or cassette carrying robot.

Then, a sheet of the semiconductor wafers W is carried out of the cassette C on a single sheet basis from the substrate carrying in/out mechanism 2 in the substrate carrying in/out mechanism section U2, is once positioned
5 by the mechanism 2, and provided to the substrate providing/receiving section 8 in the process unit section PU.

Then, the semiconductor wafer W is carried to the
10 gas processing section by the arm 17 of the substrate carrying mechanism 10 in the process unit section PU, undergoes the hydrophobing processing in the gas processing section, set for a predetermined temperature, for example, a processing temperature in the coating
15 processing section COT, in the temperature adjusting section, and then carried to the coating processing section COT by the arm 17 of the substrate carrying mechanism 10.

As a process for the arm 17 of the mechanism 10 to
20 provide the semiconductor wafer W in the coating processing section COT, the arm 17 of the mechanism 10 that holds the semiconductor wafer W enters a position for providing/receiving the semiconductor wafer W in the coating processing section COT, the supporting pin 105
25 moves up by the air cylinder 106 to hold the semiconductor wafer W while separating the semiconductor wafer W from the arm 17 of the mechanism 10, and thus the wafer W is

provided/received. Then, the arm 17 of the mechanism 10 escapes outside the coating processing section COT, the carrying-in/out opening 120 is closed by the cover 121, and the processing chamber is sealed. The supporting pin 5 105 that supports the semiconductor wafer W moves down by the air cylinder 106, and the semiconductor wafer W is provided from the supporting pin 105 onto the chuck 102 and is held thereon in vacuum adsorption. At this point, it is substantially confirmed that the 10 semiconductor wafer W is provided to the coating processing section COT by checking whether or not a predetermined pressure is maintained using a vacuum sensor. After this confirmation, the substantial coating process proceeds.

15 In addition, during the carrying process, the air from the air supplying mechanism 100 is recovered only from the gas recovery mechanism 117 and is not recovered from the gas/liquid recovery mechanism 112, or the recovery amount from the gas recovering mechanism 117 20 is set to be larger than that from the gas/liquid recovery mechanism 112. In this way, the air from the air supplying mechanism 100 is not pulled into the cup 110 and recovered from outside the cup 110 (first peripheral region α), whereby it is possible to reduce particles adhered to 25 the semiconductor wafer w in the cup 110 and to improve the yield in the processing on the semiconductor wafer W.

Next, in the coating process, after the cup 110 moves up, the semiconductor wafer W held on the chuck 102 in the cup 110 is rotated by the chuck 102, and by the movement of the arm 130, the specific nozzle 134 selected from among the resist nozzle group 132 supplies the resist solution to the center and its vicinity of the processing surface of the semiconductor wafer W. In addition, herein, for conveniences, the semiconductor wafer W is rotated and then the resist solution is supplied to the semiconductor wafer W. However, it may be possible to supply the resist solution to the semiconductor wafer W, moves the cup 110 up and rotate the semiconductor wafer W, or to move the cup 110 up, supply the resist solution to the semiconductor wafer W, and rotate the semiconductor wafer W. In this way, the film of resist solution is formed on the semiconductor wafer W.

During the coating process, the air from the air supplying mechanism 100 is recovered from the gas recovery mechanism 117 and gas/liquid recovery mechanism 112. At this point, the exhaust amount from the gas/liquid recovery mechanism 112 is larger than that in the carrying process. In other words, since the resist solution on the semiconductor wafer W is scattered in the direction of cup 110 by the rotation, it is required to exhaust so as to pull the scattered resist solution downwardly (region inside the cup 110 to exhaust (second peripheral region β)). However, since it is necessary to maintain

the constant pressure inside the processing chamber (when the pressure inside the processing chamber is not maintained constant, changes in pressure have significant effects on uniformity of the thickness of the resist film), it is required to decrease the exhaust amount exhausted from outside the cup 110 (first peripheral region α) by an increase in exhaust amount exhausted from inside the cup 110. The exhaust amount of the gas recovery mechanism 117 is thus controlled by the control mechanism 31.

10 In addition, moving the cup 110 up during the coating process is to cause the cup 110 to be closer to the air inject opening of the air supplying mechanism 100 to limit the air taken inside the cup 110 to the air from the air supplying mechanism 100, so as to prevent the air outside
15 the cup 110 from being flown in and entering the cup 110. In other words, by thus changing currents of the air inside the processing chamber, the required currents are set before the processing and during the processing. By thus setting, it is possible to prevent, for example,
20 unnecessary particles from entering the inside the cup 110 due to changes in exhaust, etc. from outside the cup 110, and to improve the yield in the processing on the semiconductor wafer W.

Next, in a process (edge remover process) of removing
25 the resist film on the periphery portion of the semiconductor wafer W among the resist film coated on the processing surface of the semiconductor wafer W, the

arm 140 moves the rotation direction $\theta 11$, and supplies the solvent from the solvent nozzle 142 to the resist film on the periphery portion of the semiconductor wafer W rotating, and thus the unnecessary film is removed.

5 In this process, the back nozzle 107 also discharges the thinner liquid to remove the unnecessary film adhered to the back of the semiconductor wafer W. In addition, the state of the cup and the operation on the air supply amount from the air supplying mechanism 100, exhaust
10 amount from the liquid recovery mechanism 117 and exhaust amount from the gas/liquid recovery mechanism 112 are set at respective values the same as those in the coating process consecutively.

Subsequently, the state of the cup and the operation
15 on the air from air supplying mechanism 100, liquid recovery mechanism 117 and the gas/liquid recovery mechanism 112 are set for respective states the same as those in the carrying process, and the semiconductor wafer W is provided from the supporting pin 105 to the arm 17
20 of the substrate carrying mechanism 10 in the reverse order to the carrying process, and the processing in the coating processing section COT is finished.

Then, the semiconductor wafer W undergoes the thermal processing in a predetermined selected thermal
25 processing section disposed at a position above the substrate providing/receiving sections 8 and 9, is transferred by the arm 17 of the substrate carrying

mechanism 10 to a predetermined selected thermal adjusting section disposed at a position below the substrate providing/receiving sections 8 and 9 to be set for the predetermined temperature, is provided to the interface unit section IFU through the substrate providing/receiving section 9, further provided to the exposure apparatus 3 from the interface unit section IFU, and undergoes exposure processing.

The semiconductor wafer W subjected to the exposure processing is provided to the interface unit section IFU, and returned to the process unit section PU through the substrate providing/receiving section 9. Further, the semiconductor wafer W undergoes the thermal processing in a predetermined selected thermal processing section disposed at a position above the substrate providing/receiving sections 8 and 9 (particularly, in the case of resist film using exposure light with a frequency of 157 nm, while supplying clear air or nitrogen with moisture less than or equal to 45%, preferably less than or equal to 10%, more preferably less than equal to 5% and more than 0% to the processing chamber in the thermal processing section, the thermal processing is executed with such moisture maintained and the predetermined pressure set), then is transferred by the arm 17 of the substrate carrying mechanism 10 to a predetermined selected thermal adjusting section disposed at a position below the substrate

providing/receiving sections 8 and 9 to be set for the predetermined temperature, and carried to the development processing section DEV.

As a process for the arm 17 of the substrate carrying mechanism 10 to provide the semiconductor wafer W in the development processing section DEV, the arm 17 of the mechanism 10 that holds the semiconductor wafer W enters a position for providing/receiving the semiconductor wafer W in the development processing section DEV, the supporting pin 36 in the holding mechanism 35 moves up by the air cylinder 50 to hold the semiconductor wafer W while separating the semiconductor wafer W from the arm 17 of the mechanism 10, and thus the wafer W is provided/received. Then, the arm 17 of the mechanism 10 escapes outside the development processing section DEV, the carrying-in/out opening 80 is closed by the cover 81, and the processing chamber is sealed. The supporting pin 36 that supports the semiconductor wafer W moves down by the air cylinder 50, and the semiconductor wafer W is provided from the supporting pin 36 onto the chuck 32 and is held thereon in vacuum adsorption. At this point, it is substantially confirmed that the semiconductor wafer W is provided to the development processing section DEV by checking whether or not a predetermined pressure is maintained using a vacuum sensor. After this confirmation, the substantial development process proceeds. When it is not confirmed that the semiconductor

wafer W is actually provided to the development processing section DEV by the vacuum sensor, in case that the semiconductor wafer W is not provided and the operation in a subsequent process is executed, there arises risks
5 that the semiconductor wafer W is broken or the processing is not executed appropriately.

In addition, during the carrying process, the air from the air supplying mechanism 30 is recovered only from the gas/liquid recovery mechanism 77 and is not
10 recovered from the gas/liquid recovery mechanism 71, or the recovery amount from the gas/liquid recovering mechanism 77 is set to be larger than that from the gas/liquid recovering mechanism 71. In this way, the air from the air supplying mechanism 100 is not pulled into
15 the cup 110 and recovered from outside the cup 110 (first peripheral region α), whereby it is possible to reduce particles adhered to the semiconductor wafer w in the cup 60 and to improve the yield in the processing on the semiconductor wafer W. (The carrying process is as
20 described above.)

After the carrying process, in the case of a process of supporting the semiconductor wafer W on the supporting pin 36 to fill the developing solution, the supporting pin 36 is moved up from the chuck 32 that holds the
25 semiconductor wafer W by the air cylinder 50, the semiconductor wafer W is again provided on the supporting pin 36 from the chuck 32, and the supporting pin 36 and

cup 60 are moved relatively to set a positional relationship between the cup 60 and the semiconductor wafer W on the supporting pin 36 as shown in FIG.4C, and the processing flow shifts to the substantial development process.

In the development process, the development nozzle 90 moves in the horizontal direction X5 while discharging the developing solution from above the cup 60, the developing solution is supplied to the cup 60 and semiconductor wafer W at the same time and filled on the semiconductor wafer W by a predetermined amount, and thus the development processing proceeds. After the solution is filled, the cup 60 is moved up so as to reduce the effect of the air from the air supplying mechanism 30 (in other words, a head portion of the cup 60 is set at a position higher than the processing surface of the semiconductor wafer W, preferably higher than the solution surface of the developing solution filled on the semiconductor wafer W and/or higher the developing solution to be filled. That is, the semiconductor wafer W is stored in the cup 60). In this way, since the current of air inside the processing chamber is changed, the air from the air supplying mechanism 30 is not pulled into the cup 60, and the current of air is generated toward the outside of the cup 60 above the semiconductor wafer W, and is recovered from outside the cup 60 (first peripheral region α). Therefore, it is possible reduce

the effect of the current of air on the developing solution filled on the semiconductor W inside the cup 60 and further to reduce adherence of particles contained in the current of air, and it is thereby possible to improve the yield in the processing on the semiconductor wafer W. In addition, during the process, the operation of the gas/liquid recovery mechanisms 71 and 77 in recovery of the air from the air supplying mechanism 30 is maintained at the same operation as in the carrying process. (The development first process is as described above.)

Further, after the carrying process, in the case of a process of supporting the semiconductor wafer W on the chuck 32 to fill the developing solution, the supporting pit 36 and cup 60 are moved relatively to set a positional relationship between the cup 60 and the semiconductor wafer W on the supporting pin 36 as shown in FIG.4C, and the processing flow shifts to the substantial development process.

In the development process, the development nozzle 95 moves in the horizontal direction X5 while discharging the developing solution from above the cup 60, and the developing solution is supplied to the cup 60 and semiconductor wafer W at the same time and filled on the semiconductor wafer W by a predetermined amount.

Then, the supporting pin 36 is moved up from the chuck 32 that holds the semiconductor wafer W by the air cylinder 50, the semiconductor wafer W is again provided

on the supporting pin 36 from the chuck 32, and the development processing on the semiconductor wafer W is continued to proceed.

In addition, in the above process, the cup 60 is
5 moved up so as to reduce the effect of the air from the air supplying mechanism 30 (in other words, a head portion of the cup 60 is set at a position higher than the processing surface of the semiconductor wafer W, preferably higher than the liquid surface of the developing solution filled
10 on the semiconductor wafer W and/or higher than the developing solution to be filled. That is, the semiconductor wafer W is stored in the cup 60). In this way, since the current of air inside the processing chamber is changed, the air from the air supplying mechanism 30 is not pulled into
15 the cup 60, and the current of air is generated toward the outside of the cup 60 above the semiconductor wafer W, and is recovered from outside the cup 60 (first peripheral region α). Therefore, it is possible to reduce the effect of the current of air on the developing solution
20 filled on the semiconductor W inside the cup 60 and further to reduce adherence of particles contained in the current of air, and it is thereby possible to improve the yield in the processing on the semiconductor wafer W. In addition, during the process, the operation of the
25 gas/liquid recovery mechanisms 71 and 77 in recovery of the air from the air supplying mechanism 30 is maintained at the same operation as in the carrying process. (The

development second process is as described above.)

Both in the development first and second processes, subsequently, the supporting pin 36 that supports the semiconductor wafer W is moved down by the air cylinder 50, and the semiconductor wafer W is provided from the supporting pin 36 onto the chuck 32 and is held on the chuck 32 in vacuum adsorption.

In addition, by selecting the development first process, particularly as compared with the development second process, since the semiconductor wafer W is supported in point-contact, it is possible to suppress fluctuations of temperatures between an area in contact with the semiconductor wafer W and the area in non-contact with the wafer better than in the surface contact, and to improve the yield of the semiconductor wafer W. Further, in supplying the processing solution to the semiconductor wafer W, the processing solution is prevented from entering the back of the semiconductor wafer W to further move to the center portion of the back of the wafer W, and it is thereby possible to maintain the inside of the processing chamber or semiconductor wafer W at cleaner state. By selecting the development second process, particularly as compared with the development first process, since the semiconductor wafer W is in surface-contact in supplying the processing solution, it is possible to further suppress the displacement of the semiconductor wafer W due to the flow

rate of the processing solution, force applied between the processing solution nozzle and semiconductor wafer W caused by the surface tension of the developing solution, etc. Furthermore, the solution is filled on the semiconductor wafer W effectively when the processing solution is supplied while rotating the semiconductor wafer W, for example, when a processing solution-supplying region of the processing solution nozzle is less than a diameter of the semiconductor.

Then, the chuck 32 is rotated at the number of rotations not to cause the developing solution on the semiconductor wafer W to spill, the rinse nozzle 91 supplies pure water and/or an aqueous solution obtained by adding a surfactant to pure water by an amount not to cause the developing solution on the semiconductor wafer W to spill, and the concentration of the developing solution on the semiconductor wafer W is diluted to a predetermined value (developing solution diluting process). As the reason for thus diluting the developing solution, in a latter half of the development process, it is possible to decrease unevenness of soluble product in the developing solution on the semiconductor wafer W partially generated by the soluble product dissolved in the developing solution, and to suppress generation of variations in partial critical dimension.

Thereafter, the rinse nozzle 91 supplies pure water, the semiconductor wafer W is rotated at high speed by

the chuck 32 to substitute for the developing solution to be dried (rinse dry process). In this process, the air from the air supplying mechanism 30 is recovered from the gas/liquid recovery mechanism 77 and gas/liquid recovery mechanism 71. At this point, the exhaust amount from the gas/liquid recovery mechanism 71 is larger than that in the carrying process. In other words, since the developing solution on the semiconductor wafer W is scattered in the direction of cup 60 by the rotation, it is required to exhaust so as to pull the scattered developing solution downwardly (region inside the cup 60 to exhaust (second peripheral region β)). However, since it is necessary to maintain the constant pressure inside the processing chamber (when the pressure inside the processing chamber is not maintained constant, changes in pressure have significant effects on uniformity in the development processing), it is required to decrease the exhaust amount exhausted from outside the cup 60 (first peripheral region α) by an increase in exhaust amount exhausted from inside the cup 60. The exhaust amount of the liquid/gas recovery mechanism 77 is thus controlled by the control mechanism 31.

Then, the state of the cup and the operation on a supply amount of the air from air supplying mechanism 30, exhaust amount from the gas/liquid recovery mechanism 77 and exhaust amount from the gas/liquid recovery mechanism 71 are set for respective states the same as

those in the carrying process, and the semiconductor wafer W is provided from the supporting pin 36 to the arm 17 of the substrate carrying mechanism 10 in the reverse order to the carrying process, and the processing in the development processing section DEV is finished.

Then, the semiconductor wafer W undergoes the thermal processing in a predetermined selected thermal processing section disposed at a position above the substrate providing/receiving sections 8 and 9, is transferred by the arm 17 of the substrate carrying mechanism 10 to a predetermined selected thermal adjusting section disposed at a position below the substrate providing/receiving sections 8 and 9 to be set for the predetermined temperature, is carried in the cassette C through the substrate providing/receiving section 8 by the substrate carrying in/out mechanism 2 of the substrate carrying in/out mechanism section U2 in the cassette unit section CU, and a series of processing is finished.

Another embodiment of the development processing method of this embodiment will be described below. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

In the development processing method as described earlier, the developing solution is filled on the semiconductor wafer W, the cup is moved upwardly and

downwardly to change the current of air inside the processing chamber, and then the concentration of the developing solution is changed in the latter half of the development process. Generally, semiconductor plants
5 use a single kind of developing solution with a concentration of, for example, 2.38%. However, resist patterns are made finer depending on devices, and an unexpected event occurs that the concentration is too high in development speed. Therefore, a method will be
10 described below of diluting the concentration of developing solution filled on the semiconductor wafer in the first half of the development process.

When such processing is required, in the case of the development first process, the developing solution
15 is filled on the semiconductor wafer W by a predetermined amount, the rinse nozzle 91 supplies pure water and/or an aqueous solution obtained by adding a surfactant to pure water by an amount not to cause the developing solution on the semiconductor W to spill while maintaining the
20 liquid state, and the concentration of the developing solution on the semiconductor W is diluted to a predetermined value

Further in the development second process, the developing solution is supplied to the cup 60 and
25 semiconductor wafer W at the same time, the developing solution is filled on the semiconductor wafer W by a predetermined amount, the chuck 32 is rotated at the number

of rotations not to cause the developing solution on the semiconductor W to spill while maintaining the liquid state, the rinse nozzle 91 supplies pure water and/or an aqueous solution obtained by adding a surfactant to pure water by an amount not to cause the developing solution on the semiconductor W to spill, and the concentration of the developing solution on the semiconductor W is diluted to a predetermined value.

Then, the supporting pin 36 is moved up from the chuck 32 that holds the semiconductor wafer W by the air cylinder 50, the semiconductor wafer W is again provided onto the supporting pin 36, and the development processing on the semiconductor wafer W is continued to proceed. Accordingly, after the developing solution is diluted, moving the cup 60 changes the current of air inside the processing chamber.

Also in such development first and second processes, the process as described earlier (developing solution diluting process) may be further added. Moreover, as another processing for not performing the developing solution diluting process, for example, a rinse drying process may be performed in which after the semiconductor wafer W is provided from the supporting pin 36 onto the chuck 32 and held on the chuck 32 in vacuum adsorption, the chuck 32 is rotated at the first number of rotations to cause the developing solution on the semiconductor wafer W to be once blown off, or to remain by a predetermined

amount, i.e. before the developing solution is not dried up, the rinsing solution is supplied to the processing surface of the semiconductor wafer W that rotates at the second number of rotations less than the first number of rotations, and then the semiconductor wafer W is rotated at the third number of rotations more than or approximately equal to the first number of rotations to dry. Thus, it is possible to perform the processing as appropriate corresponding to the resist film formed on the semiconductor wafer W.

Another embodiment of the supporting mechanism 35 of this embodiment will be described below with reference to FIGs. 7A and 7B. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

As shown in FIGs. 7A and 7B, the supporting mechanism 35 is provided with a plurality of supporting members 200 which supports the back of the semiconductor wafer W in partial line-contact, for example, arranged at regular intervals on concentric circumference of the semiconductor wafer W, a ring member 37 as a solution penetration preventing mechanism that is provided outside the supporting members 200 and prevents the processing solution such as the developing solution and rinsing solution from entering a center portion of the back of the semiconductor wafer W, and a plurality of supporting

poles that supports in one piece the ring member 37 and supporting members 200. The ring member 37 and supporting member 200 of the supporting mechanism are provided with a tilting portion 41 so that a position of the height thereof is lower toward the center of the semiconductor wafer W (in the direction of from the ring member 37 to the supporting member 200). Such a configuration prevents the rinsing solution or developing solution adhered to the asperity portion 40 or the rinsing solution that discharged from the back nozzle 51 to rinse the ring member 37, etc. from adhering to at least a contact portion 201 in contact with the semiconductor wafer W of the supporting mechanism 35. By thus configuring, it is possible to prevent the rinsing solution or developing solution from adhering to the semiconductor wafer in the progress of the processing or subsequent semiconductor wafer W, and it is thereby possible to suppress occurrences of partial temperature change of the semiconductor wafer W or generation of particles in the system caused by the rinsing solution or developing solution adhered to the semiconductor wafer W being dried, and to improve the yield of the semiconductor wafer W.

Further, as shown in FIG. 7B, heights and positions of supporting members 200 and ring member 37 are set so that supporting members 200 are higher by a predetermined length, for example, a length (L in the figure) ranging from 0.5 mm to 5 mm. It is because of preventing the ring

member 37 from coming into direct contact with the back of the semiconductor. The contact portion 201 of the supporting member 200 to be in contact with the back of the semiconductor W is formed of, for example, an elastic member, as a member having a higher coefficient of friction and lower thermal conductivity than those of a member 39 forming the supporting member 200 and also as a displacement preventing member that prevents occurrences of horizontal displacements including horizontal displacements in supporting the back of the semiconductor W and further in supplying the solution to the semiconductor wafer W after supporting the back of the semiconductor W. The low thermal conductivity prevents occurrences of a risk that the uniformity in the surface is inhibited due to effects such as the heat escaping from the semiconductor wafer W through the contact portion with the supporting member 200 during the processing of the semiconductor wafer W. As materials for the contact portion 201, examples include engineering plastics such as PEEK · PBI, ceramics such as alumina · zirconium and rubbers such as perfluoro-compounds.

In this embodiment, since the supporting members 200 are configured to support the back of the semiconductor wafer W in a plurality of partial line-contacts, it is possible to support the semiconductor wafer W in horizontal state as compared to point-contact. Therefore, it is possible to decrease the distance between

the ring member 37 and the back of the semiconductor wafer W, and to prevent the processing solution from entering the center portion of the back of the semiconductor wafer W.

5 Further, since the friction to support the back of the semiconductor wafer W is increased as compared to the point-contact, it is possible to prevent the semiconductor wafer W from being displaced horizontally. In addition, when the line-contact of the supporting
10 member 200 is excessively increased, for example, in the form of a ring, there is a risk that ring-shaped unevenness occurs on the processing surface of the semiconductor wafer W in the processing on the semiconductor wafer W. Accordingly, it is required to set line-contact to the
15 extent of not causing the processing unevenness on the processing surface of the semiconductor wafer W. However, in the foregoing, it is described that a ring-shaped supporting member 200 is not preferable as an above example, as a matter of course, a ring-shaped member is not denied
20 when the specification allows the shape of a ring.

Another embodiment of the supporting mechanism 35 and back nozzle 51 in this embodiment will be described below. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same
25 reference numerals to omit specific descriptions thereof.

The process of discharging pure water from back nozzle 51 is used to rinse and remove the developing

solution and/or pure water held in the asperity portion 40 of the ring member 37 using the surface tension or washing the developing solution or others adhered to the back of the semiconductor wafer W, after the development process and the process of diluting the developing solution held in the asperity portion 40 of the ring member 37 using the surface tension. However, before the processing solution is supplied to the semiconductor wafer W, i.e. before the development process, the back nozzle 51 discharges pure water to the asperity portion 40 of the ring member 37, so that the pure water film is temporarily formed between the ring member 37 and the back of the semiconductor wafer W using the surface tension. In this way, the concentration of the developing solution between the ring member 37 and the back of the semiconductor wafer W is decreased after the development process, thereby facilitating the rinsing and enabling decreased rinsing time and reduced mists.

Referring to FIGs. 8A and 8B, another embodiment will be described below in the relationship between gas/liquid recovery mechanisms 71, 77 and 112, gas recovery mechanism 117 and cups 60 and 110 of this embodiment. In addition, the structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof. For conveniences, the description is given with reference to the development processing section DEV.

As shown in FIG.8A, the cup 60 is connected to a cup moving mechanism that moves upwardly and downwardly, for example, air cylinder 209, and is configured to be movable upwardly and downwardly. A wall 210 is disposed
5 between the cup 60 and gas/liquid recover mechanism 77 (gas recover mechanism 117 in COT) that exhausts the air/liquid from a region outside the cup 60, and on the wall 210 is provided, as shown in FIG.8B, a ventilation opening 211 to form the current of air 212 for causing
10 the ambient air inside the cup 60 to flow into the gas/liquid recover mechanism 77 (gas recover mechanism 117 in COT) at the same as the upward movement of the cup 60 by the air cylinder 209. The gas variation mechanism is thus configured.

15 Such a configuration is capable of eliminating the gas/liquid recover mechanism 71. In COT, adding the liquid recover function to the gas recover mechanism 117 is capable of eliminating the gas/liquid recover mechanism 112, resulting in an advantage that the system
20 is miniaturized. Further, since a single exhaust mechanism allows control inside the processing chamber, the control is made easy to maintain the pressure inside the processing chamber in the relationship in air between the air supplying mechanisms 30 and 100, and it is possible
25 to reduce effects on the processing of the semiconductor wafer W in the processing chamber, and to improve the yield of the processing.

In addition, the gas variation mechanism is not limited to the above-mentioned embodiment, as long as a mechanism generates variations in the current of air. For example, as long as the air is exhausted from inside the cup at the same time as or based on the movement of the cup, any physical or electrical mechanisms are available. Further, by thus configuring, in the case of making an exhaust amount from the first peripheral region approximately equal to an exhaust amount from the first and second peripheral regions, even the cup 60 moves upwardly and downwardly mechanically, since the entire amount of the exhaust is always constant, the control is made easy and the system is miniaturized. Furthermore, when the exhaust area of the first peripheral region is different from the exhaust area of the second peripheral region, for example, the exhaust area of the first peripheral region is larger than the exhaust area of the second peripheral region, a single exhaust system works automatically at the same time as the upward and downward movement of the cup 60, whereby the control is further made easy, and it is also possible to improve the stability of the pressure inside the processing chamber. As a result, it is possible to improve the yield of the processing on the substrate. Moreover, when the exhaust time in the first peripheral region is different from the exhaust time in the second peripheral region, for example, the exhaust time in the first peripheral region

is longer than the exhaust time in the second peripheral region, a single exhaust system works automatically at the same time as the upward and downward movement of the cup 60, whereby the control is further made easy, and
5 it is also possible improve the stability of the pressure inside the processing chamber. As a result, it is possible to improve the yield of the processing on the substrate.

Referring to FIG.9, another embodiment will be
10 described below of the cup 60 in development processing section DEV of this embodiment. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

15 A cup 220 is provided with a rectangular portion 221 in the form of a rectangle and a cylindrical portion 223 in the form of a cylinder provided inside the rectangular portion 221 with a head portion 225 projecting. The rectangular portion 221 (having a form of the cup
20 60 provided with the rectangular portion 221) is provided with a recover opening 222 that recovers the processing solution such as the developing solution discharged from the development nozzle 90 and pure water discharged from the rinse nozzle 91, and the processing solution recovered
25 from the recover opening 222 is recovered by a liquid recover mechanism 226. In addition, a region (first region) surrounded by the rectangular portion 221 is set

to be larger in size than a region (second region) surrounded by the cylindrical portion 223.

Since the cup 220 is thus configured, the rectangular portion 221 is capable of recovering the development solution discharged from the development nozzle 90 and pure water discharged from rinse nozzle 91, and it is possible to configure the gas/liquid recover mechanism 77 as a mechanism that recovers only the gas, and reduce the size of the system corresponding to the reduced mechanism. Further, since it is possible to suppress adherence of processing solution such as the developing solution and rinsing solution to the wall portion 75 forming the first peripheral region α , the processing chamber can be cleaner and it is possible to suppress generation of mist/particle. The developing solution adhered to the rectangular portion 221 is rinsed by pure water discharged from the rinse nozzle 91.

The processing in the cup 220 carries out in the same processing procedures as described earlier. The processing surface of the semiconductor wafer W is set to be the same height or higher as/than the head portion 225 (at this point, in the first region as a region surrounded by the rectangular portion 221), the development nozzle 90 moves horizontally, and concurrently supplies the developing solution to the processing surface of the semiconductor wafer W and the head portion 225 of the cup 220, and thus the developing

solution is filled on the processing surface of the semiconductor wafer W. In addition, the positional relationship between the head portion 225 and the semiconductor wafer w is set in the same way as in the positional relationship between the cup 60 and wafer W, and when the form of the head portion 225 is defined as the same form of a head portion of the cup 60, the same effects as described earlier are obtained. Further, the height of the head portion 225 is set higher than the height of the processing surface of the semiconductor wafer W to obtain the above-mentioned effects, and by thus setting, it is possible to further suppress effects of the current of air in exhaust from outside the head portion 225 on the developing solution filled on the processing surface of the semiconductor wafer W, and to improve the yield of the processing.

Then, as described earlier, the cup 220 is moved up, and the semiconductor wafer W is placed in a region (second region) enclosed by the cylindrical portion 223 to proceed the development processing. Thus, since the cup 220 is formed of the cylindrical portion 223 provided with the rectangular portion 221, the exhaust from the first peripheral region α is performed in a position away from the cylindrical portion 223, and the current of air inside the processing chamber less affects the semiconductor wafer W in the cylindrical portion 223. It is thereby possible to improve the yield of the

semiconductor wafer W. In addition, although in this embodiment the first region of the cup 220 is in the form a rectangle, the region may be in the form of a circle. Further, the form of the region is not limited to the
5 above-mentioned forms, and may include any forms as long as a region (second region) enclosed by the cylindrical portion 223 is smaller in size than a region (first region) enclosed by the rectangular portion 221.

Another embodiment of the development processing
10 section DEV of this embodiment will be described with reference to FIGs. 10 and 11. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

15 In this embodiment, a wall 250 is provided above the rectifying mechanism 74 as an enclosing member, and is configured to divide a region (first peripheral region α) to exhaust from between the cup 60 and wall portion 75. In other words, for the region (second peripheral
20 region β) to exhaust from inside the cup 60, there are set a region (first peripheral region $\alpha 1$) between the cup 60 and wall 250 and a region (first peripheral region $\alpha 2$) between the wall 250 and wall portion 75. The wall 250 is set higher than the head portion of the cup 60
25 by a predetermined length (W2 in the figure). This structure prevents the developing solution from the development nozzle 90 and, for example, pure water from

the rinse nozzle 91 from adhering directly to the wall portion 75 of the processing chamber. Accordingly, the wall 250 has the function of a second cup as a liquid scattering preventing mechanism.

5 In this way, it is possible to prevent the developing solution from the development nozzle 90 and, for example, pure water from the rinse nozzle 91 from adhering directly, and when the wall 250 is detachable, it is possible to clean or exchange only the wall 250 in maintenances such
10 as cleaning of the processing chamber, and to reduce the maintenance time. Further, since it is also possible to prevent the developing solution from the development nozzle 90 and, for example, pure water from the rinse nozzle 91 from adhering to the cover 81, it is possible
15 to prevent, for example, the developing solution adhered to the cover 81 from drying, scattering in opening and closing the cover 81, and adhering to the semiconductor wafer W as particles in the processing chamber. In addition, the wall 250 is set higher than the head portion
20 of the cup 60 by a predetermined length (W2 in the figure), but is not limited to such a structure, as long as the wall 250 is spaced from the cup 60 to some extent, in other words, the wall 250 is capable of preventing the developing solution from the development nozzle 90 or,
25 for example, pure water from the rinse nozzle 91 from directly adhering to the wall portion 75 of the processing chamber.

In addition, the integrally formed supporting members 200 and ring member 37 is explained as the supporting mechanism 35, but is not limited to such a structure. For example, with the positional
5 relationship between the supporting members 200 and ring member 37 maintained as described above, the members 200 and 37 may be provided as a separate member to move upwardly and downwardly independently of each other as an upward/downward mechanism, and operate as appropriate
10 to perform the predetermined processing. Further, any other methods are available as long as the effectiveness of the supporting members 200 and ring member 37 is implemented.

Another embodiment of the supporting mechanism 35
15 of this embodiment will be described with reference to FIGs.12A and 12B. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

20 As shown in FIGs.12A and 12B, the supporting mechanism 35 is provided with a plurality of supporting members 200 that supports the back of the semiconductor wafer W in partial line-contact, a ring member 37 as a solution penetration preventing mechanism that is
25 provided outside the supporting members 200 and prevents the processing solution such as the developing solution or rinsing solution from entering a center portion of

the back of the semiconductor wafer W, and a plurality of supporting poles 38 that supports in one piece the ring member 37 and supporting members 200.

5 The asperity portion 40 of the ring member 37 is provided with a solution-supplying opening 420 that supplies the rinsing solution, and the rinsing solution is arbitrarily supplied from a rinsing solution-supplying source 415 via piping 413. The ring member 37 is provided with a plurality of rinse nozzles 411 that supplies, for
10 example, sprays the rinsing solution, for example, cleaning solution from the rinsing solution supplying source 415 at least to the ring member 37 and tilting portion 41. A center portion 410 of the tile portion 41 is in the form of a mountain, and on its surface is provided
15 a groove 412 to promote the drain as in the side wall of the ring member 37.

By thus configuring the supporting mechanism 35, the solution supplying opening 420 that supplies the rinsing solution has the effectiveness that the water
20 film formed with the back of the semiconductor wafer W is more reliable than in the supply from the back nozzle 51. In this case, it may be possible to use the back nozzle 51 together, or form the water film only using the rinsing solution from the solution supplying opening 420. It is
25 possible to clean the asperity portion 40 and the ring member 37 more reliably after the development process. Further, the rinsing solution is injected from the

solution supplying opening 420 and rinse nozzle 411, and the solution is drained efficiently by the groove 412, whereby it is possible to clean the ring member 37 more reliably and faster, to prevent mists adhered to the ring member 37 from being generated as particles when the ring member 37 dries, and to increase the yield of the semiconductor wafer W. In addition, it is preferable that the rinsing solution from the rinse nozzle 411 and/or back nozzle 51 does not adhere to the contact portion 201 in contact with the back of the semiconductor wafer W. The reason is that it is possible to prevent the rinsing solution or developing solution from adhering to the semiconductor wafer W in the progress of the processing or subsequent semiconductor wafer W, to suppress occurrences of partial temperature change of the semiconductor wafer W or generation of particles in the system caused by the rinsing solution or developing solution adhered to the semiconductor wafer W being dried, and to improve the yield of the semiconductor wafer W.

Still another embodiment of the supporting mechanism 35 of this embodiment will be described with reference to FIG.13. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

As shown in FIG.13, in the supporting mechanism 35, the plurality of rinse nozzles 411 provided in the rinse

member 37 supplies the rinsing solution from the rinsing solution supplying source 415. The supporting mechanism 35 is further provided with a plurality of gas nozzles 417 (for conveniences, a signal nozzle is shown in the figure) that injects gas such as, for example, cleaning air and nitrogen from a gas supplying mechanism 416.

By thus configuring, it is possible to implement the drying process more reliably and faster after the development process and subsequent rinsing by the rinse nozzles 411, and to improve the throughput of the processing.

Still another embodiment of the supporting mechanism 35 of this embodiment will be described with reference to FIG.14. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

As shown in FIG.14, in the supporting mechanism 35, the plurality of rinse nozzles 411 provided in the rinse member 37 supplies the rinsing solution from the rinsing solution supplying source 415 through a valve VA1, and is configured to enable injection of gas such as, for example, cleaning air and nitrogen from a gas supplying mechanism 416 through a valve V2.

In this way, since the rinse nozzles 411 is capable of discharging the rinsing solution and gas selectively as appropriate by switching between valves V1 and V2,

discharging the gas after discharging the rinsing solution from the rinse nozzles 411 allows the rinsing solution adhered to the nozzles 411 to be blown off, and it is thus possible to implement the drying process more reliably and faster after rinsing, and to improve the throughput. Further, the need is eliminated of providing the rinse nozzle and gas nozzle separately, it is possible to simplify and reduce in size the system of the ring member 37.

Referring to FIG.15, an embodiment will be described of a location of a storage container that stores processing solutions used in the coating processing section COT and/or development processing section DEV as solution processing apparatuses in the resist processing apparatus 1 of this embodiment. In addition, the same structural elements as those in the above-mentioned embodiment are assigned the same reference numerals to omit specific descriptions thereof.

As shown in FIG.15, the storage container 499 is placed at a position below the interface unit section IFU. The position is located below, by the distance V101 in the vertical direction, the providing section 4 or receiving section 5 which provides or receives a substrate to/from the exposure apparatus 3 and which is disposed below, by the distance V100 in the vertical direction, the lower portion of the substrate carrying in/out opening 19 of the substrate receiving and providing sections 8

and 9.

Setting such a position is to suppress adverse effects as possible such as deterioration of processing solution, for example, resist solution or developing solution due to thermal effects. In other words, the reason for placing the container at a position below the substrate carrying in/out opening 19 is to prevent the heat from the thermal processing section or others in the process unit section PU from being conveyed through the substrate carrying in/out opening 19. The reason for placing the container at a position below the providing section 4 or receiving section 5 which provides or receives a substrate to/from the exposure apparatus 3 is to prevent the heat from being conveyed from the exposure apparatus 3 through the providing section 4 or receiving section 5. Further, it is possible to suppress the heat from walls, because the heat propagation from the substrate carrying in/out section 19, providing section 4 and/or receiving section 5 affects upper portions of walls rather than the lower portions. Furthermore, the interface unit section IFU is configured so that the downflow DF with the controlled temperature directly acts on at least the substrate carrying in/out opening 19, providing section 4 and/or receiving section 5, and thus configured to relieve the heat propagation from the substrate carrying in/out opening 19, providing section 4 and/or receiving section 5.

In order to further suppress the heat from the wall partitioning the interface unit section IFU and process unit section PU, exhaust of processing sections in the process unit section PU, for example, a plurality of development processing sections DEV (a plurality of coating processing sections COT) is collectively performed on cassette-unit-section side in a respective block, and exhaust passages 501 and 501 are formed for each block. Similarly, in thermal processing sections in the process unit section PU, exhaust passages (not shown) are formed and provided on cassette-unit-section side for each block or each of the same kind of thermal processing sections related in the processing temperature.

As a position for placing the storage containers each storing a processing solution practically used in the coating processing section COT and/or development processing section DEV, for example, resist solution or developing solution, it is considered to place the container at positions 504 and 505 below the processing sections in the process unit section PU, for example, a plurality of development processing sections DEV (a plurality of coating processing sections COT). In this case, it is not preferable to place the storage containers at regions immediately below the exhaust passages 501 and 502 for each block or to place the containers in contact with walls in which the exhaust passages 501 and 502 are

provided. It is preferable to place the container spaced from a position immediately below the exhaust passages 501 and 502 for each block by the distances H100 and H101 in the horizontal direction (for eliminating the effect of heat), respectively.

Further, with respect to a position of disposing a control apparatus, as a heat source of the solution processing apparatus 1, which controls the entire apparatus, it is not preferable to dispose the control apparatus in the interface unit section IFU or in the process unit section PU, and it is preferable to dispose the control apparatus in the cassette unit section CU. Furthermore, in order to prevent the heat from being conveyed to each processing section in the process unit section PU or being conveyed to the interface unit section IFU through the process unit section PU, the position is located above the upper portion of the substrate carrying in/out opening 19 of the substrate providing/receiving sections 8 and 9 by the distance V102 in the vertical direction.

As described above, also in consideration of the effects of heat inside the apparatuses, it is possible to suppress, for example, deterioration of the processing solution, while suppressing thermal effects on the substrate, and to improve the yield of the substrate.

Further, as a substrate as described above, a semiconductor wafer is used to explain, however, the

substrate is not limited to the wafer, and may be, for example, a glass substrate such as LCD substrate, or a substrate of a disk such as CD. The solution processing is not limited to development and coating, may be used
5 in other apparatuses such as a cleaning apparatus, and further is not limited to the above cases, as long as methods and apparatuses use a processing solution.

As described above, the present invention allows exhaust mainly from the first peripheral region around
10 the substrate undergoing the processing and further from the second peripheral region between the first peripheral region and the substrate, thereby enabling reduced effects of the current of air on the developing solution on the substrate and further enabling the developing
15 solution for use in development processing to act on the exposed resist on the substrate, and thus provides advantages of enhancing the uniformity in the processing on the substrate and improving the yield according to the processing on the substrate.

20 The above-mentioned embodiments intend to clarify the technical ideas of the present invention and not restrictive, and the present invention is not limited the above-mentioned embodiments and is capable of being carried into practice with various modifications thereof
25 without departing from the scope of the present invention.

This application is based on the Japanese Patent Application No.2002-244352 filed on, July 22, 2002,

entire content of which is expressly incorporated by reference herein.